

In the Claims

Please add new claims 38-49 in accordance with 37 C.F.R. § 1.121(c)(1)(i). A marked up version showing amendments is not required.

D1 38.¹³ (new) A capacitor construction comprising a first capacitor electrode over a substrate, a capacitor dielectric layer over the first electrode, a second capacitor electrode over the dielectric layer, and an atomic layer deposited metal-containing conductive layer between the first and second electrodes.

39.¹⁴ (new) The construction of claim 38.¹³ wherein the atomic layer deposited conductive layer is on the first electrode.

40.¹⁵ (new) The construction of claim 38.¹³ wherein the atomic layer deposited conductive layer comprises elemental metal, a metal alloy, or a metal-containing compound.

41.¹⁶ (new) The construction of claim 38.¹³ wherein the atomic layer deposited conductive layer comprises WN, WSiN, TaN, TiN, TiSiN, Pt, Pt alloys, Ir, Ir alloys, Pd, Pd alloys, RuO_x, or IrO_x.

42.¹⁷ (new) The construction of claim 38.¹³ wherein at least one of the first or second electrode comprises polysilicon and the dielectric layer comprises oxygen.

- 43.¹⁸ A capacitor construction comprising:
- a first capacitor electrode over a substrate;
 - a metal-containing conductive material over the first electrode, the material comprising a chemisorption product of first and second precursor layers;
 - a capacitor dielectric layer over the first electrode; and
 - a second capacitor electrode over the dielectric layer.

- 44.¹⁹ (new) The construction of claim 43¹⁸ wherein the first and second precursor layers each consist essentially of a monolayer.

- 45.²⁰ (new) The construction of claim 43¹⁸ wherein the first and second precursors respectively comprise only one of the following pairs: WF_6/NH_3 , $\text{TaCl}_5/\text{NH}_3$, $\text{TiCl}_4/\text{NH}_3$, tetrakis(dimethylamido)titanium/ NH_3 , ruthenium cyclopentadiene/ H_2O , $\text{IrF}_5/\text{H}_2\text{O}$, organometallic $\text{Pt}/\text{H}_2\text{O}$.

- 46.²¹ (new) The construction of claim 43¹⁸ wherein the atomic layer deposited conductive material is on the first electrode.

- 47.²² (new) The construction of claim 43¹⁸ wherein the atomic layer deposited conductive material comprises elemental metal, a metal alloy, or a metal containing compound

- 48.²³ (new) The construction of claim 43¹⁸ wherein the conductive material comprises WN , WSiN , TaN , TiN , TiSiN , Pt , Pt alloys, Ir , Ir alloys, Pd , Pd alloys, RuO_x , or IrO_x .

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49.²⁴ (new) The construction of claim ¹⁸43 wherein at least one of the first or second electrode comprises polysilicon and the dielectric layer comprises oxygen.